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#### November 2013

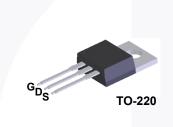
### FQP65N06 N-Channel QFET<sup>®</sup> MOSFET 60 V, 65 A, 16 mΩ

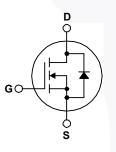
#### Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

#### Features

- 65 A, 60 V,  $R_{DS(on)}$  = 16 m $\Omega$  (Max.) @ V<sub>GS</sub> = 10 V, I<sub>D</sub> = 32.5 A
- Low Gate Charge (Typ. 48 nC)
- Low Crss (Typ. 100 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating





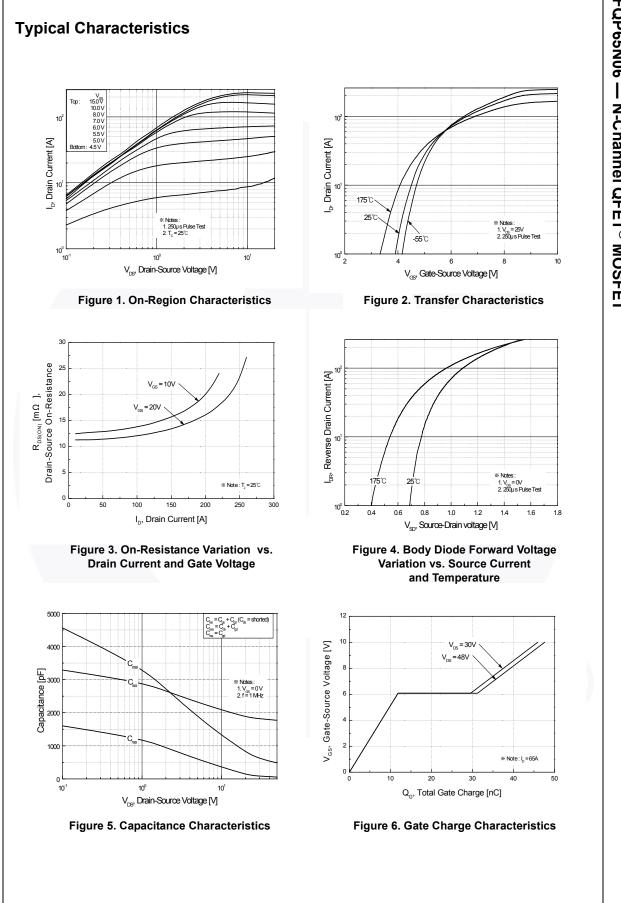
#### Absolute Maximum Ratings T<sub>c</sub> = 25°C unless otherwise noted.

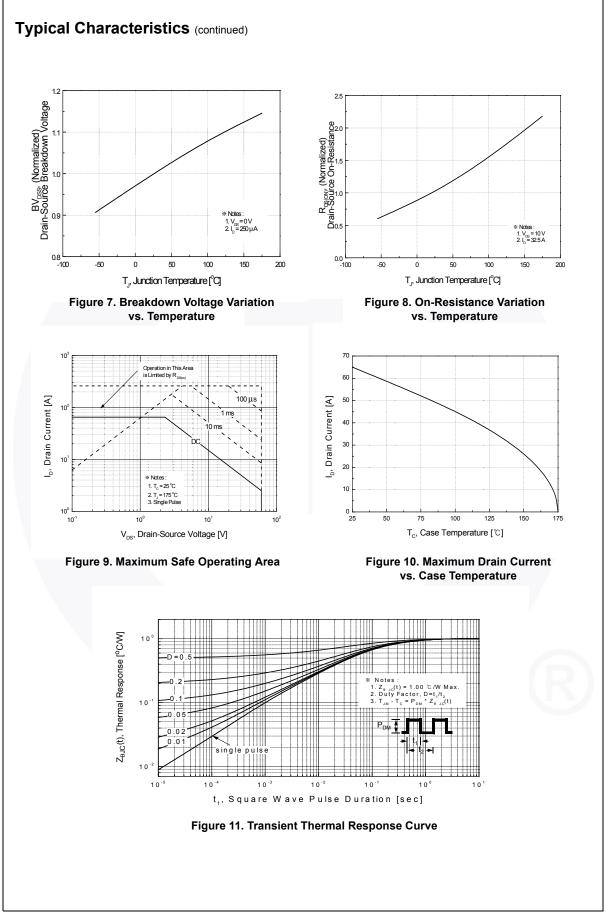
| Symbol                            | Parameter  |             | FQP65N06    | Unit |
|-----------------------------------|--|-------------|-------------|------|
| V <sub>DSS</sub>                  | Drain-Source Voltage   |             | 60          | V    |
| I <sub>D</sub>                    | Drain Current - Continuous (T <sub>C</sub> = 25°                   | C)          | 65          | A    |
|                                   | - Continuous (T <sub>C</sub> = 100                                 | )°C)        | 46.1        | A    |
| I <sub>DM</sub>                   | Drain Current - Pulsed   | (Note 1)    | 260         | A    |
| V <sub>GSS</sub>                  | Gate-Source Voltage  |             | ± 25        | V    |
| E <sub>AS</sub>                   | Single Pulsed Avalanche Energy                                     | (Note 2)    | 650         | mJ   |
| I <sub>AR</sub>                   | Avalanche Current  | (Note 1) 65 |             | A    |
| E <sub>AR</sub>                   | Repetitive Avalanche Energy  | (Note 1)    | 15.0        | mJ   |
| dv/dt                             | Peak Diode Recovery dv/dt  | (Note 3)    | 7.0         | V/ns |
| PD                                | Power Dissipation (T <sub>C</sub> = 25°C)                          |             | 150         | W    |
|                                   | - Derate above 25°C  |             | 1.00        | W/°C |
| T <sub>J</sub> , T <sub>STG</sub> | Operating and Storage Temperature Range                            |             | -55 to +175 | °C   |
| ΤL                                | Maximum Lead Temperature for Solderir 1/8" from Case for 5 seconds | ng,         | 300         | °C   |

### **Thermal Characteristics**

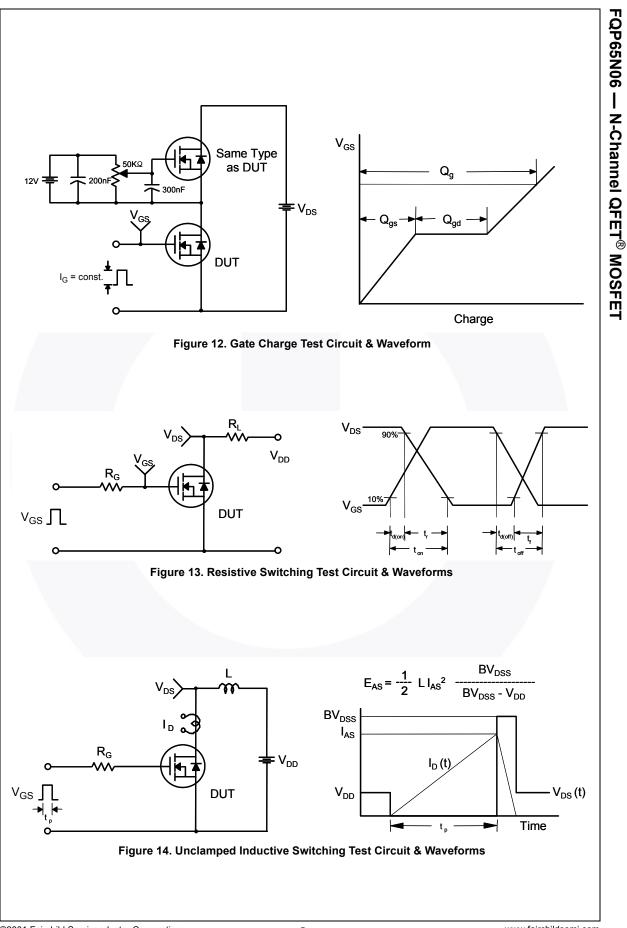
| Symbol                | Parameter                                     | FQP65N06 | Unit |  |
|-----------------------|---|----------|------|--|
| $R_{\theta JC}$       | Thermal Resistance, Junction-to-Case, Max.    | 1.00     | °C/W |  |
| $R_{	extsf{	heta}JA}$ | Thermal Resistance, Junction-to-Ambient, Max. | 62.5     | °C/W |  |

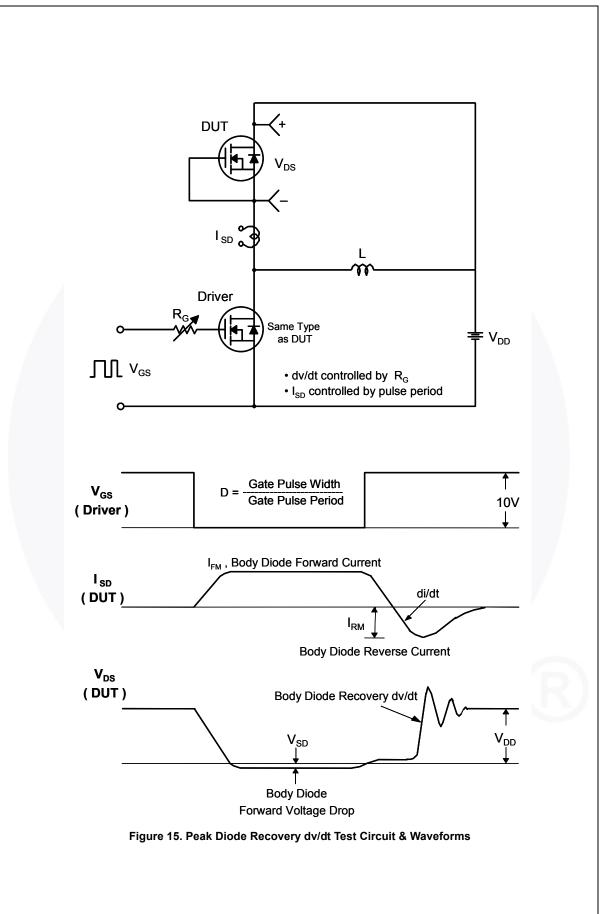
| Part NumberTop MarkPackageFQP65N06FQP65N06TO-220 |         | Package  | e Packing Method Re   |  | Size   | Tape Width |     | h Q         | Quantity    |          |
|--|---------|--|-----------------------|--|--------|------------|-----|-------------|-------------|----------|
|  |         | Tube N/A   |                       | /A   | N/A    |            | 5   | 50 units    |             |          |
| lectri   | cal C   | naracteristics   | T <sub>C</sub> = 25°C | unless otherwise noted.                                    |        |            |     |             |             |          |
| Symbol   |         | Parameter  |                       | Test Cond  | itions |            | Min | Тур         | Max         | Unit     |
| Off Cha  | aracte  | istics   |                       |  |        |            |     |             |             |          |
| V <sub>DSS</sub>                                 | 1       | Source Breakdown V   | oltage                | V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250                | ) uA   |            | 60  |             |             | V        |
| BV <sub>DSS</sub><br>ΔT <sub>J</sub>             |         | down Voltage Temper  | U                     | $I_D = 250 \ \mu\text{A}, \text{Reference}$                |        | 25°C       |     | 0.07        |             | V/°C     |
| DSS  |         |  |                       | V <sub>DS</sub> = 60 V, V <sub>GS</sub> =                  | 0 V    |            |     |             | 1           | μA       |
|  | Zero G  | Sate Voltage Drain Cu  | urrent                | $V_{DS} = 48 \text{ V}, \text{ T}_{C} = 18$                | 50°C   |            |     |             | 10          | μA       |
| GSSF   | Gate-E  | Body Leakage Currer  | t, Forward            | V <sub>GS</sub> = 25 V, V <sub>DS</sub> =                  | 0 V    | 1          |     |             | 100         | nA       |
| SSSR   |         | Body Leakage Currer  |                       | $V_{GS}$ = -25 V, $V_{DS}$ =                               |        |            |     |             | -100        | nA       |
| On Cha   | aracter | istics   |                       |  |        |            |     |             |             |          |
| GS(th)   | Gate 1  | hreshold Voltage   |                       | $V_{DS} = V_{GS}, I_D = 25$                                | 0 μΑ   |            | 2.0 |             | 4.0         | V        |
| RDS(on)  |         | Drain-Source<br>sistance   |                       | $V_{GS}$ = 10 V, I <sub>D</sub> = 32.5                     | 5A     |            |     | 0.012       | 0.016       | Ω        |
| FS   | Forwa   | rd Transconductance  |                       | V <sub>DS</sub> = 25 V, I <sub>D</sub> = 32                | 2.5 A  |            |     | 48          |             | S        |
| viss<br>voss                                     | Input ( | racteristics<br>Capacitance<br>t Capacitance   |                       | V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 1<br>f = 1.0 MHz | 0 V,   |            |     | 1850<br>700 | 2410<br>910 | pF<br>pF |
| rss  |         | se Transfer Capacita   | nce                   | 1 1.0 10112  |        |            |     | 100         | 130         | pF       |
|  |         |  |                       |  |        |            |     |             |             |          |
| Switch   | · · ·   | aracteristics  |                       |  |        |            |     |             | 1           |          |
| l(on)  |         | n Delay Time   |                       | V <sub>DD</sub> = 30 V, I <sub>D</sub> = 32                | 2.5 A, |            |     | 20          | 50          | ns       |
|  |         | In Rise Time   |                       | R <sub>G</sub> = 25 Ω                                      |        |            |     | 160         | 330         | ns       |
| l(off)   | Turn-C  | off Delay Time   |                       |  |        |            |     | 90          | 190         | ns       |
|  | Turn-C  | off Fall Time  |                       |  | (N     | lote 4)    |     | 105         | 220         | ns       |
| ) <sup>g</sup>                                   | Total C | Bate Charge  |                       | V <sub>DS</sub> = 48 V, I <sub>D</sub> = 65                | 5 A,   |            |     | 48          | 65          | nC       |
| ) <sub>gs</sub>                                  | Gate-S  | Source Charge  |                       | V <sub>GS</sub> = 10 V                                     |        |            |     | 12          |             | nC       |
| l <sub>gd</sub>                                  | Gate-I  | Drain Charge   |                       |  | (N     | lote 4)    |     | 19.5        |             | nC       |
| )rain-S  | Source  | Diode Characte   | eristics an           | d Maximum Ra   | tinas  |            |     |             |             |          |
| 3  |         | um Continuous Drair  |                       |  | U      |            |     |             | 65          | А        |
| SM   | Maxim   | um Pulsed Drain-So   | urce Diode Fo         | orward Current   |        |            |     |             | 260         | А        |
| SD   |         | Source Diode Forwar  | 1                     | $V_{GS} = 0 V, I_{S} = 65 A$                               | A      |            |     |             | 1.5         | V        |
| r  |         | se Recovery Time   |                       | $V_{GS} = 0 V, I_S = 65 A,$                                |        |            |     | 62          |             | ns       |
| l<br>Prr   |         | se Recovery Charge   |                       | $dI_{\rm F} / dt = 100  {\rm A}/{\mu s}$                   |        |            |     | 110         |             | nC       |
|  |         | in the second seco |                       |  |        |            |     |             |             |          |

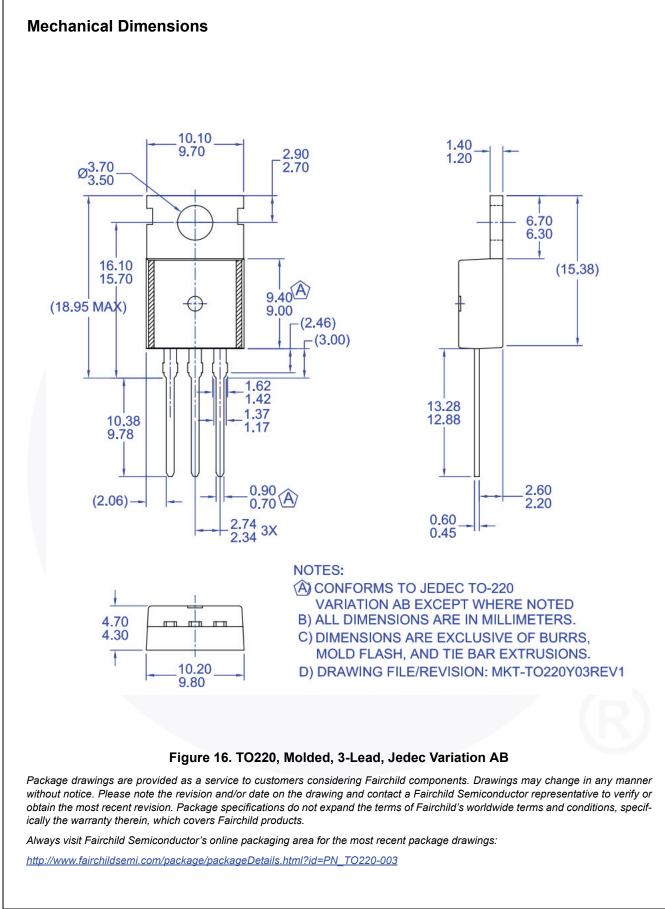




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